

This device is designed for VHF/UHF amplifier, oscillator and mixer applications. As a common gate amplifier, 16 dB at 100 MHz and 12 dB at 450 MHz can be realized. Sourced from Process 92.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units | |
|----------------------------------|--|-------------|-------|--|
| V _{DS} | Drain-Source Voltage | 25 | V | |
| V _{GS} | Gate-Source Voltage | - 25 | V | |
| I _{GF} | Forward Gate Current | 10 | mA | |
| T _J ,T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C | |

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

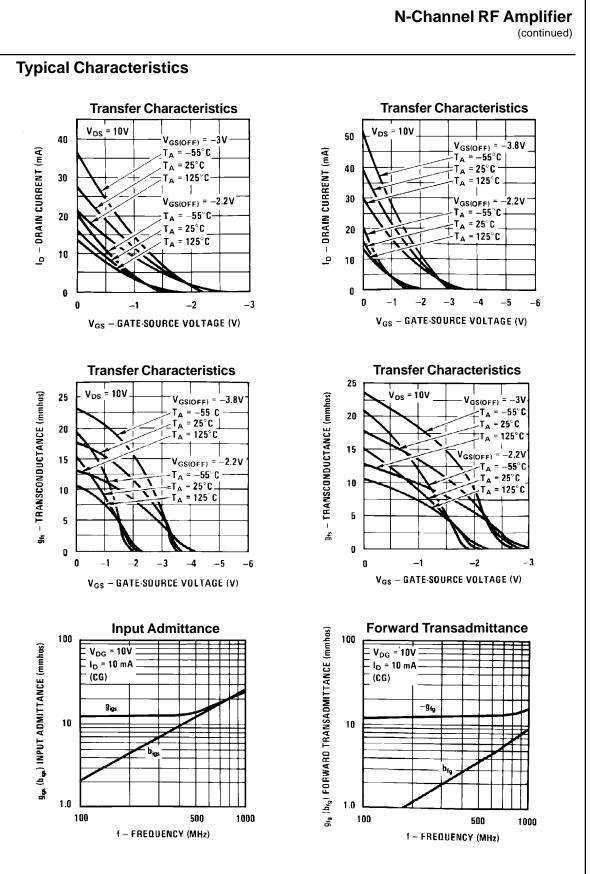
| Symbol | Characteristic | Мах | | Units |
|-----------------------|---|-----------|---------------|-------|
| | | J309-J310 | *MMBFJ309-310 | |
| PD | Total Device Dissipation | 625 | 350 | mW |
| | Derate above 25°C | 5.0 | 2.8 | mW/°C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 125 | | °C/W |
| $R_{	extsf{	heta}JA}$ | Thermal Resistance, Junction to Ambient | 357 | 556 | °C/W |

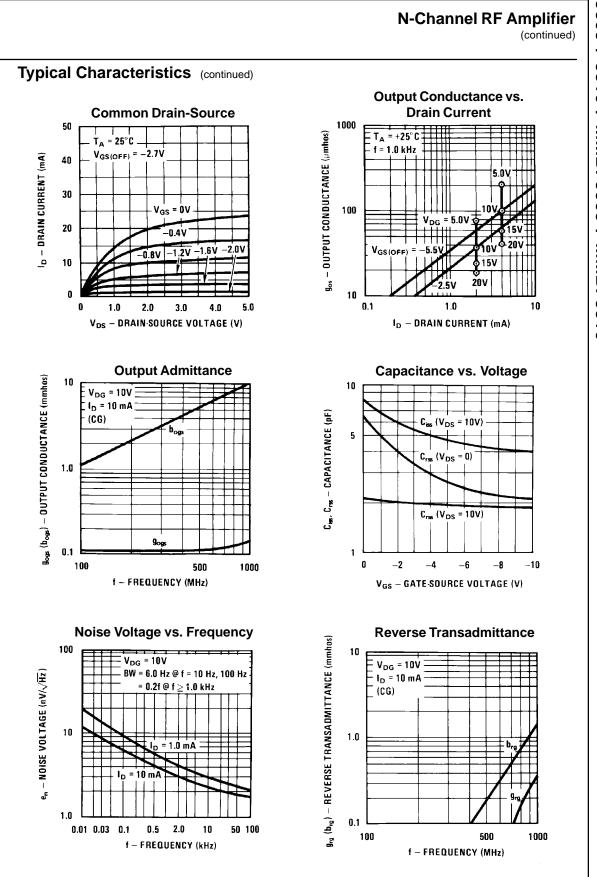
*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

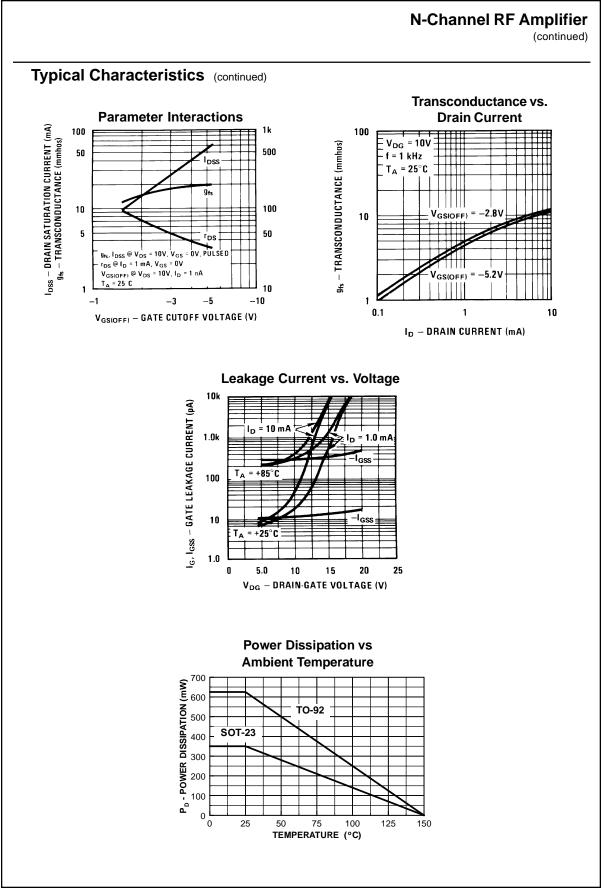
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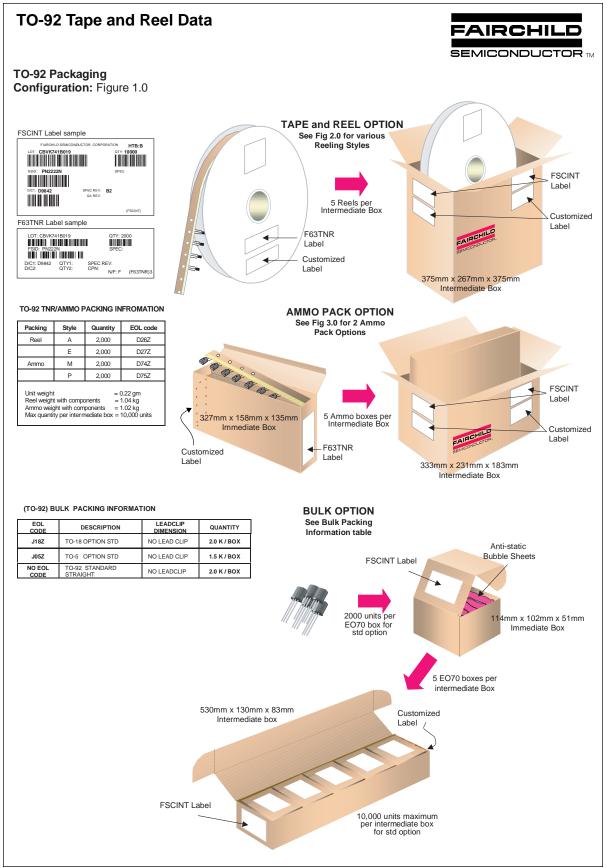
N-Channel RF Amplifier (continued)

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units |
|---|---|--|----------------|--|----------------------|--|
| • | | | | | | |
| OFF CHA | RACTERISTICS | | | | | |
| V _{(BR)GSS} | Gate-Source Breakdown Voltage | $I_G = -1.0 \ \mu A, \ V_{DS} = 0$ | - 25 | | | V |
| I _{GSS} | Gate Reverse Current | $V_{GS} = -15 V, V_{DS} = 0$ $V_{GS} = -15 V, V_{DS} = 0, T_A =$ $125^{\circ}C$ | | | - 1.0 - 1.0 | nA μA |
| V _{GS(off)} | Gate-Source Cutoff Voltage | $V_{DS} = 10 \text{ V}, \text{ I}_D = 1.0 \text{ nA}$ 309 310 | - 1.0 - 2.0 | | - 4.0 - 6.5 | V V |
| ON CHAF | RACTERISTICS | | | | | |
| I _{DSS} | Zero-Gate Voltage Drain Current* | $V_{DS} = 10 V, V_{GS} = 0$ 309 310 | 12 24 | | 30 60 | mA mA |
| V _{GS(f)} | Gate-Source Forward Voltage | $V_{DS} = 0, I_G = 1.0 \text{ mA}$ | | | 1.0 | V |
| Re ₍ y _{is)} | Common-Source Input Conductance | $V_{DS} = 10, I_D = 10 \text{ mA}, f = 100 \text{ MHz}$ 309 | | 0.7 | | mmho |
| Re ₍ y _{is)} | Common-Source Input Conductance | 309 | | 0.7 | | mmhos |
| (-) | • | | | 0.7 0.5 0.25 | | mmhos mmhos mmhos |
| Re _(yos) | Conductance Common-Source Output Conductance | 309 310 V _{DS} = 10, I _D = 10 mA, f = 100 MHz | | 0.5 0.25 | | mmhos |
| Re(y _{os)} G _{pg} | Conductance Common-Source Output Conductance Common-Gate Power Gain Common-Source Forward | 309 310 | | 0.5 | | mmho: mmho: dB |
| Re(y _{os)} G _{pg} Re(y _{fs)} | Conductance Common-Source Output Conductance Common-Gate Power Gain | 309 310 V _{DS} = 10, I _D = 10 mA, f = 100 MHz V _{DS} = 10, I _D = 10 mA, f = 100 MHz | | 0.5 0.25 16 | | mmhos |
| Re(y _{os)} G _{pg} Re(y _{fs)} Re(y _{ig)} | Conductance Common-Source Output Conductance Common-Gate Power Gain Common-Source Forward Transconductance | $\begin{array}{c} 309\\ 310\\ \end{array}$ $V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \end{array}$ $V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \end{array}$ $V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \end{array}$ | 10,000 | 0.5 0.25 16 12 | 20,000 | mmhos mmhos dB mmhos mmhos |
| Re(y _{os)} G _{pg} Re(y _{fs)} Re(y _{ig)} Øfs | Conductance Common-Source Output Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward | $\begin{array}{c} \textbf{309} \\ \textbf{310} \\ \textbf{V}_{DS} = \textbf{10}, \textbf{I}_{D} = \textbf{10} \text{ mA}, \textbf{f} = \textbf{100} \text{ MHz} \\ \textbf{V}_{DS} = \textbf{10}, \textbf{I}_{D} = \textbf{10} \text{ mA}, \textbf{f} = \textbf{100} \text{ MHz} \\ \textbf{V}_{DS} = \textbf{10}, \textbf{I}_{D} = \textbf{10} \text{ mA}, \textbf{f} = \textbf{100} \text{ MHz} \\ \textbf{V}_{DS} = \textbf{10}, \textbf{I}_{D} = \textbf{10} \text{ mA}, \textbf{f} = \textbf{100} \text{ MHz} \\ \textbf{V}_{DS} = \textbf{10}, \textbf{I}_{D} = \textbf{10} \text{ mA}, \textbf{f} = \textbf{100} \text{ MHz} \\ \textbf{V}_{DS} = \textbf{10}, \textbf{I}_{D} = \textbf{10} \text{ mA}, \textbf{f} = \textbf{1.0} \text{ kHz} \\ \textbf{309} \\ \textbf{310} \\ \textbf{V}_{DS} = \textbf{10}, \textbf{I}_{D} = \textbf{10} \text{ mA}, \textbf{f} = \textbf{1.0} \text{ kHz} \end{array}$ | | 0.5 0.25 16 12 | , | mmhos mmhos dB mmhos mmhos μmhos |
| Re(Y _{os)} G _{pg} Re(Y _{fs)} Re(Y _{ig)} Øfs | Conductance Common-Source Output Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward Transconductance Common-Source Output | $\begin{array}{c} \textbf{309} \\ \textbf{310} \\ \hline \textbf{V}_{DS} = \textbf{10}, \ \textbf{I}_{D} = \textbf{10} \ \textbf{mA}, \ \textbf{f} = \textbf{100} \ \textbf{MHz} \\ \hline \textbf{V}_{DS} = \textbf{10}, \ \textbf{I}_{D} = \textbf{10} \ \textbf{mA}, \ \textbf{f} = \textbf{100} \ \textbf{MHz} \\ \hline \textbf{V}_{DS} = \textbf{10}, \ \textbf{I}_{D} = \textbf{10} \ \textbf{mA}, \ \textbf{f} = \textbf{100} \ \textbf{MHz} \\ \hline \textbf{V}_{DS} = \textbf{10}, \ \textbf{I}_{D} = \textbf{10} \ \textbf{mA}, \ \textbf{f} = \textbf{100} \ \textbf{MHz} \\ \hline \textbf{V}_{DS} = \textbf{10}, \ \textbf{I}_{D} = \textbf{10} \ \textbf{mA}, \ \textbf{f} = \textbf{100} \ \textbf{MHz} \\ \hline \textbf{V}_{DS} = \textbf{10}, \ \textbf{I}_{D} = \textbf{10} \ \textbf{mA}, \ \textbf{f} = \textbf{100} \ \textbf{MHz} \\ \hline \textbf{Mz} \\ \hline \textbf{309} \\ \textbf{310} \end{array}$ | | 0.5 0.25 16 12 | 18,000 | mmho mmho dB mmho mmho µmhos µmhos µmhos |
| Re(Yos) Gpg Re(Yfs) Re(Yig) Offs Ooss | Conductance Common-Source Output Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward Transconductance Common-Source Output Conductance Common-Gate Forward | $\begin{array}{c} \textbf{309} \\ \textbf{310} \\ \textbf{V}_{DS} = 10, \ \textbf{I}_{D} = 10 \ \textbf{mA}, \ \textbf{f} = 100 \ \textbf{MHz} \\ \hline \textbf{V}_{DS} = 10, \ \textbf{I}_{D} = 10 \ \textbf{mA}, \ \textbf{f} = 100 \ \textbf{MHz} \\ \hline \textbf{V}_{DS} = 10, \ \textbf{I}_{D} = 10 \ \textbf{mA}, \ \textbf{f} = 100 \ \textbf{MHz} \\ \hline \textbf{V}_{DS} = 10, \ \textbf{I}_{D} = 10 \ \textbf{mA}, \ \textbf{f} = 100 \ \textbf{MHz} \\ \hline \textbf{V}_{DS} = 10, \ \textbf{I}_{D} = 10 \ \textbf{mA}, \ \textbf{f} = 100 \ \textbf{MHz} \\ \hline \textbf{V}_{DS} = 10, \ \textbf{I}_{D} = 10 \ \textbf{mA}, \ \textbf{f} = 1.0 \ \textbf{kHz} \\ \hline \textbf{309} \\ \textbf{310} \\ \hline \textbf{V}_{DS} = 10, \ \textbf{I}_{D} = 10 \ \textbf{mA}, \ \textbf{f} = 1.0 \ \textbf{kHz} \\ \hline \textbf{V}_{DS} = 10, \ \textbf{I}_{D} = 10 \ \textbf{mA}, \ \textbf{f} = 1.0 \ \textbf{kHz} \\ \hline \textbf{309} \\ \textbf{309} \end{array}$ | | 0.5 0.25 16 12 12 13,000 | 18,000 | mmhos mmhos dB mmhos |
| Re(yos) Spg Re(yfs) Re(yfg) Ifs Joss Jfg Jog | Conductance Common-Source Output Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward Transconductance Common-Source Output Conductance Common-Gate Forward Conductance Common-Gate Forward Conductance Drain-Gate Capacitance | $\begin{array}{c} & 309\\ & 310\\ \hline \\ & V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \hline \\ & V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \hline \\ & V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \hline \\ & V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \hline \\ & V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & 309\\ \hline \\ & 310\\ \hline \\ & V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & 309\\ \hline \\ & 310\\ \hline \\ & V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & 309\\ \hline \\ & 310\\ \hline \\ & V_{DS} = 0, \ V_{GS} = -10 \ V, \ f = 1.0 \ \text{MHz}\\ \hline \end{array}$ | | 0.5 0.25 16 12 12 13,000 12,000 100 | 18,000 | mmho mmho dB mmho mmho <u>µmhos</u> µmhos µmhos µmhos |
| Re(yos) Spg Re(yfs) Re(yfg) Ifs Joss Ifg Jog Cdg Seg | Conductance Common-Source Output Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward Transconductance Common-Source Output Conductance Common-Gate Forward Conductance Common-Gate Forward Conductance Drain-Gate Capacitance Source-Gate Capacitance | $\begin{array}{c} & 309\\ & 310\\ \hline \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \hline \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \hline \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \hline \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \hline \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & \\ & \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & \\ & \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & \\ & \\ & \\ & \\ & \\ & \\ & \\ & \\ & $ | | 0.5 0.25 16 12 12 13,000 12,000 100 150 | 18,000 | mmho mmho dB mmho mmho <u>µmhos</u> <u>µmhos</u> <u>µmhos</u> <u>µmhos</u> <u>µmhos</u> |
| Re(Yis) Re(Yos) Gpg Re(Yfs) Re(Yig) Dfs Doss Dfg Cdg Cdg Csg NF | Conductance Common-Source Output Conductance Common-Gate Power Gain Common-Source Forward Transconductance Common-Gate Input Conductance Common-Source Forward Transconductance Common-Source Output Conductance Common-Gate Forward Conductance Common-Gate Forward Conductance Drain-Gate Capacitance | $\begin{array}{c} & 309\\ & 310\\ \hline \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \hline \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \hline \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \hline \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 100 \ \text{MHz}\\ \hline \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & \\ & \\ & \\ V_{DS} = 10, \ I_{D} = 10 \ \text{mA}, \ f = 1.0 \ \text{kHz}\\ \hline \\ & \\ & \\ & \\ & \\ & \\ & \\ & \\ & \\ & $ | | 0.5 0.25 16 12 12 13,000 12,000 100 150 2.0 | 18,000 150 2.5 | mmho mmho dB mmho mmho µmhos µmhos µmhos µmhos pF |



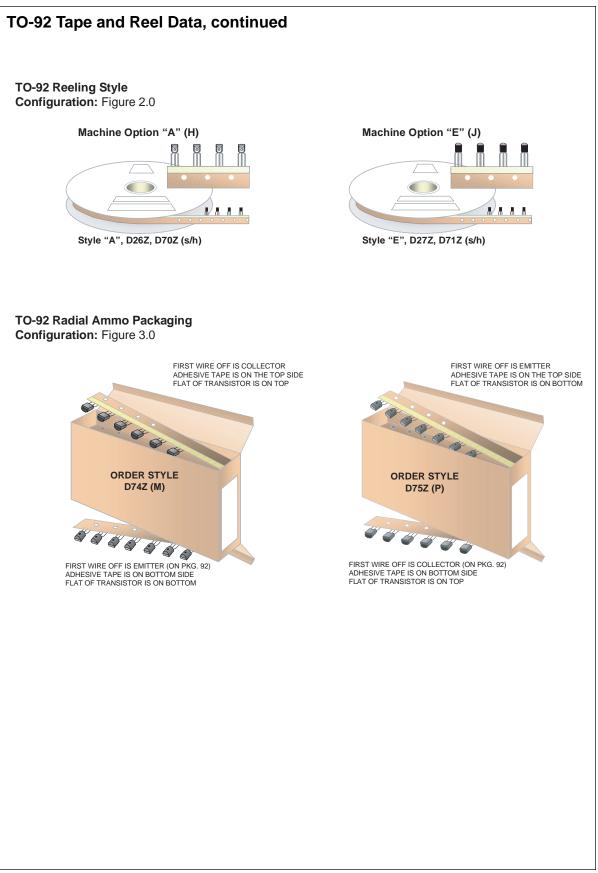


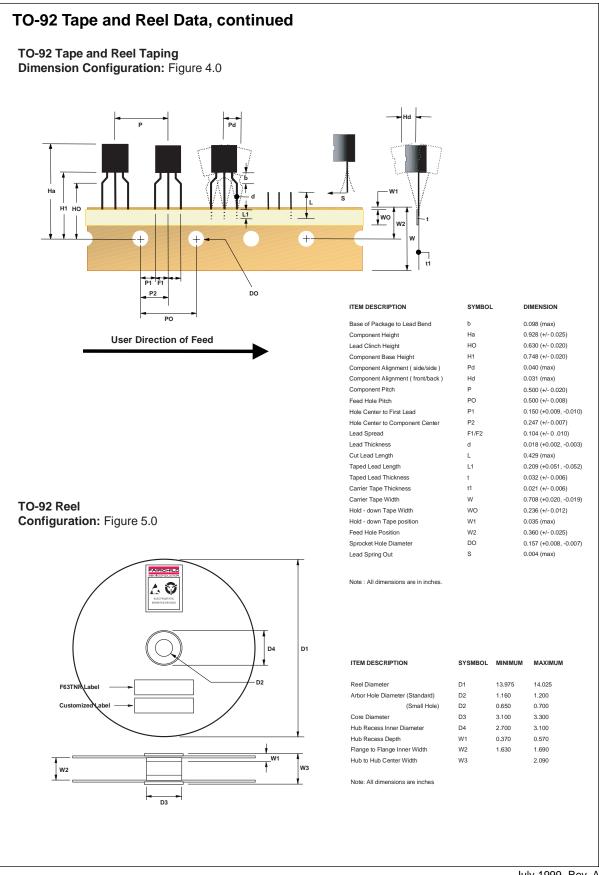




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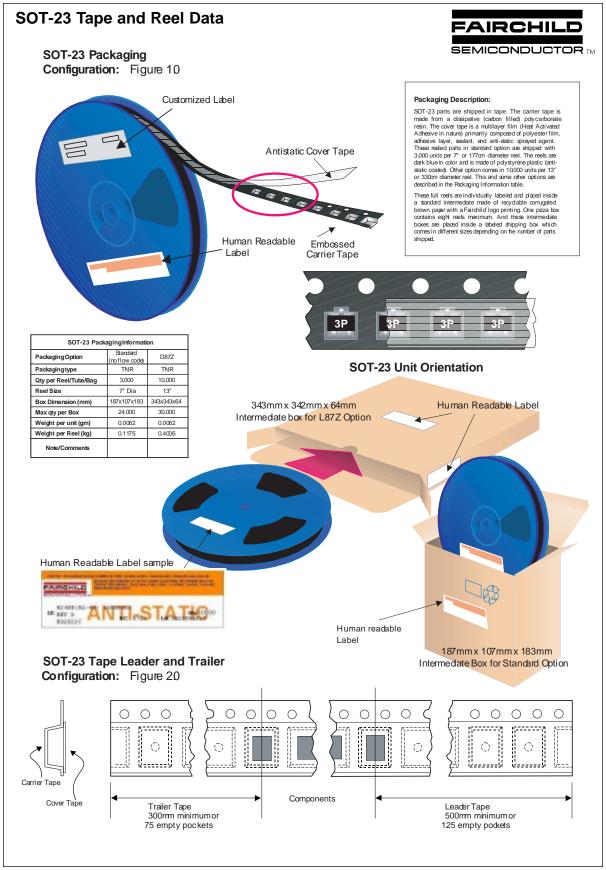
September 1999, Rev. B





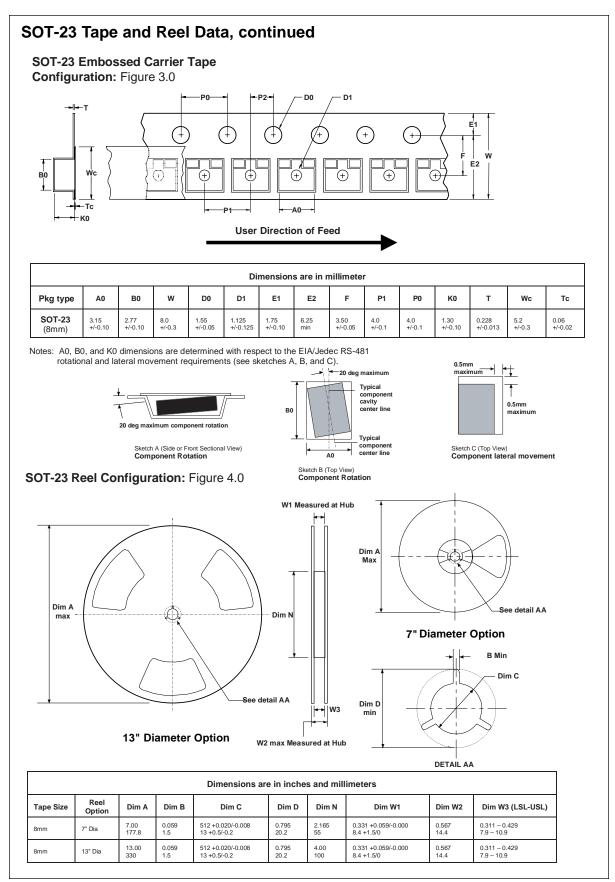
July 1999, Rev. A



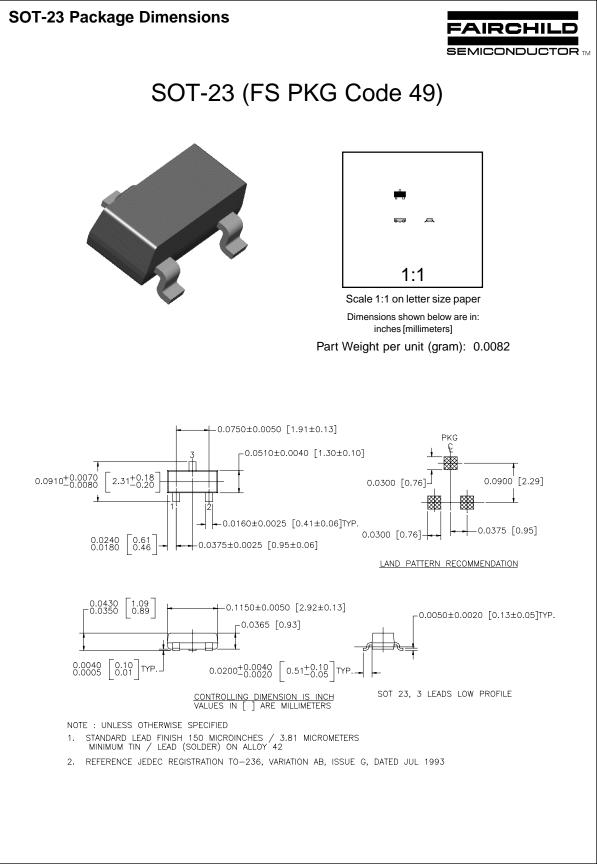


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|--------------------------|---------------------------|---|
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| | 1 | Rev G |